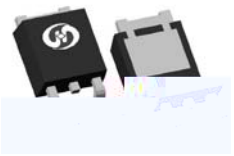
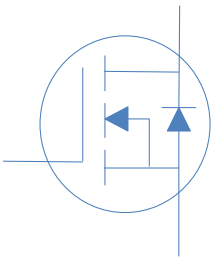
45V N-Ch Power MOSFET

DS(on),typ			
DS(on),typ			





		=25		
Avalanche Energy, Single Pulse		=25		
Power Dissipation		=25		
Operating and Storage Temperature				

Thermal Resistance Junction-Ambient			
Thermal Resistance Junction-Case			/W

Characteristics at T =25 (unless otherwise specified)

Static Characteristics

				typ		
Drain to Source Breakdown Voltage						
Gate Threshold Voltage	GS(th)					
		=25				
		=100				
	fs					
		Open, f=1MHz				

Dynamic Characteristics

Input Capacitance		=20V, f=1MHz				pF
Output Capacitance						
Reverse Transfer Capacitance						
Total Gate Charge						
Total Gate Charge						
Gate to Source Charge						
Gate to Drain (Miller) Charge						
Turn off Delay Time	d(off)					
Fall Time	f					

Reverse Diode Characteristics

Diode Forward Voltage		F				
		F /dt=200A/				
Reverse Recovery Charge						

Fig 1. Typical Output Characteristics	Figure 2. On-Resistance vs. Gate-Source Voltage

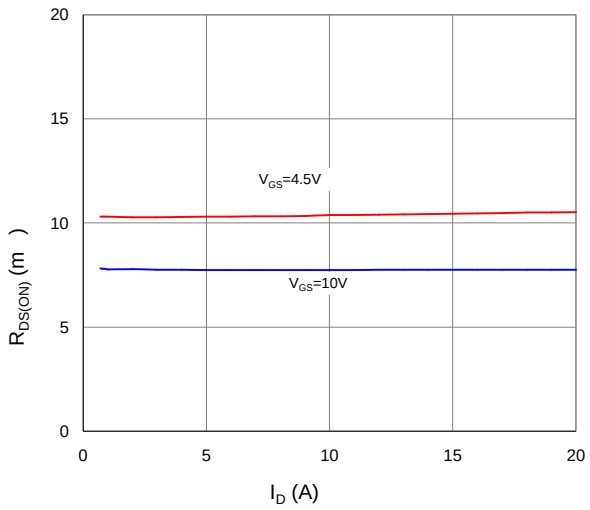
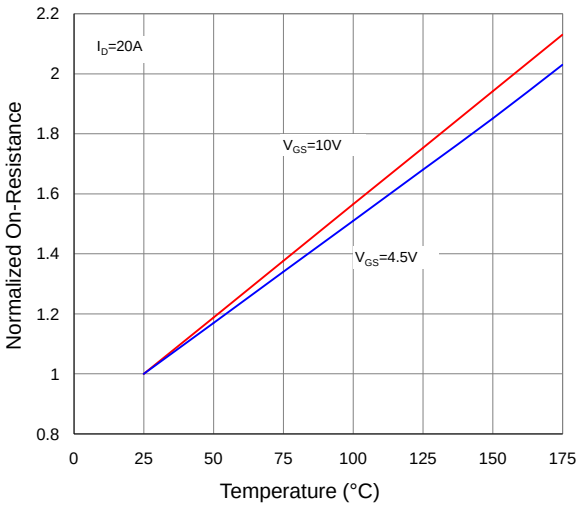
Figure 3. On-Resistance vs. Drain Current and Gate Voltage	Figure 4. Normalized On-Resistance vs. Junction Temperature
	

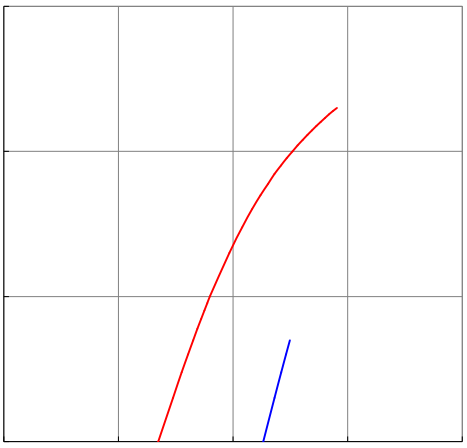
Figure 5. Typical Transfer Characteristics	Figure 6. Typical Source-Drain Diode Forward Voltage
	

Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

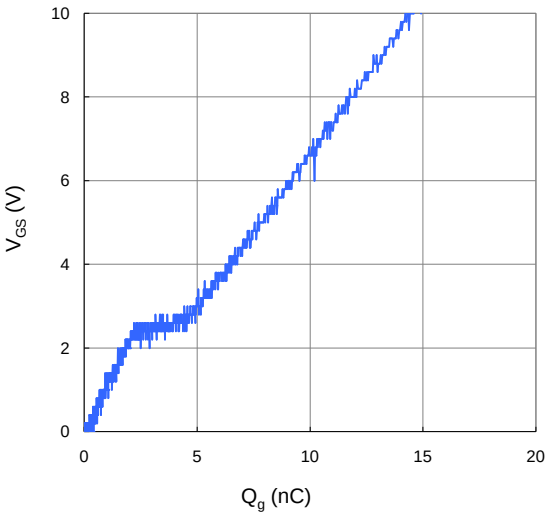


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

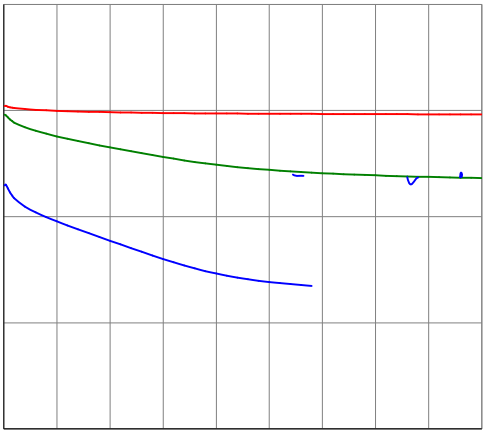


Figure 9. Maximum Safe Operating Area

Figure 10. Maximun Drain Current vs. Case Temperature

Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient